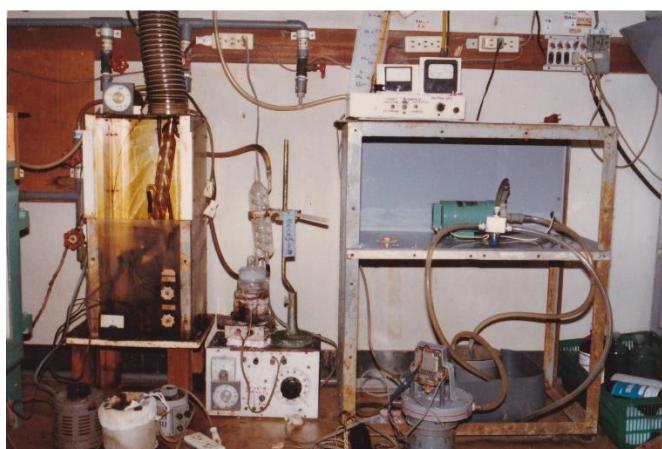
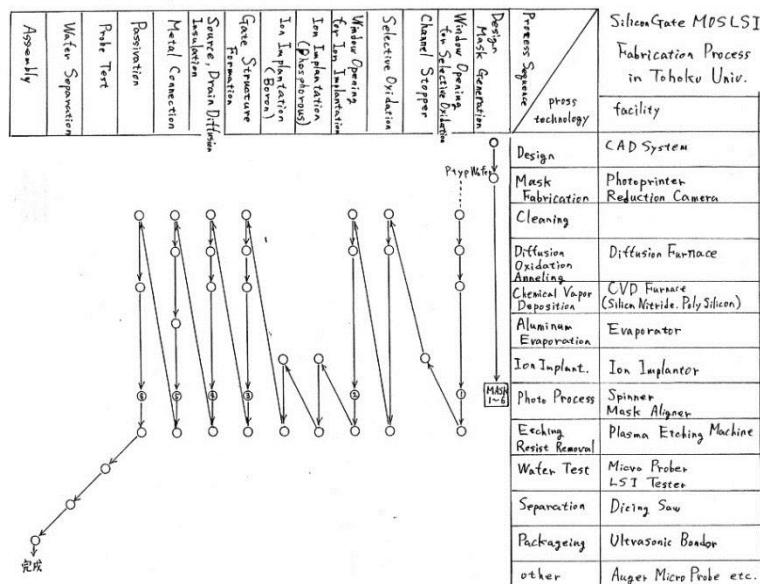
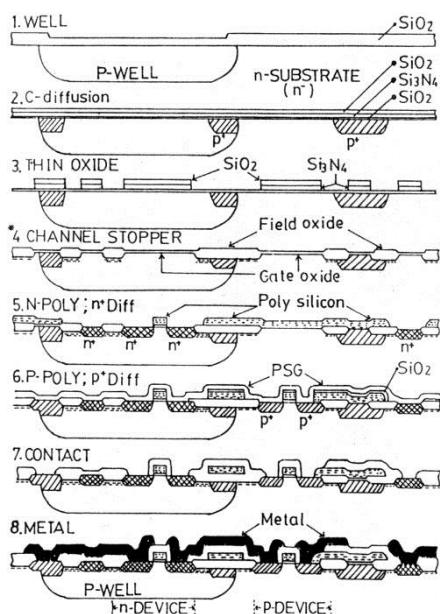
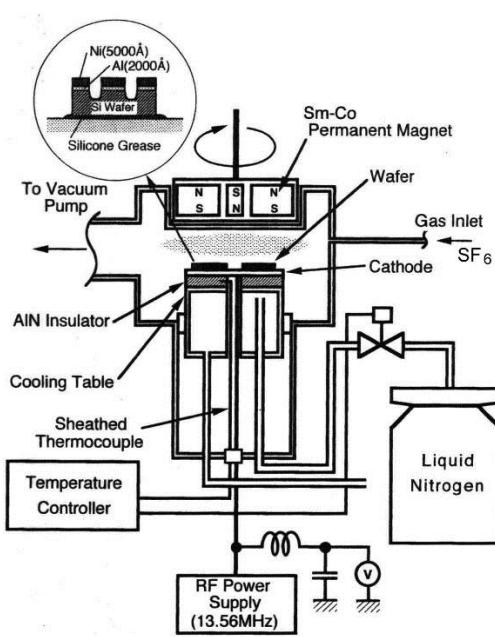


[3] Wafer process (etching, oxidation & diffusion, CVD, ion implantation, evaporation & sputter deposition)

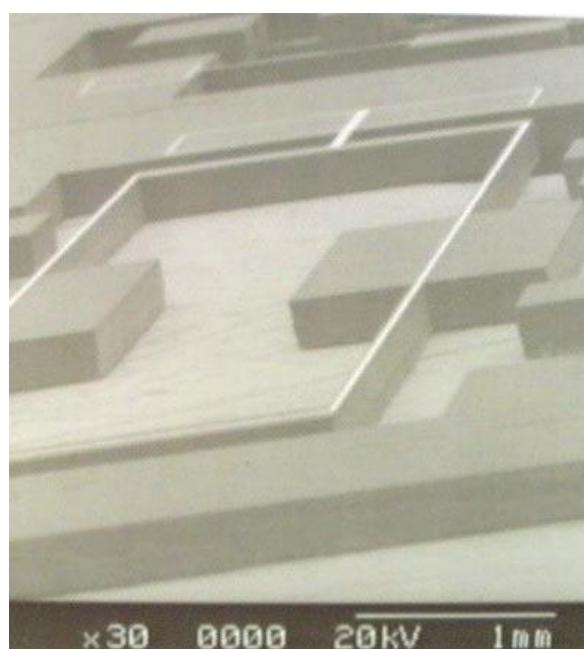


Si EPW etcher, SiN etcher in hot phosphoric acid, Electrochemical Si etcher

DI watersupply



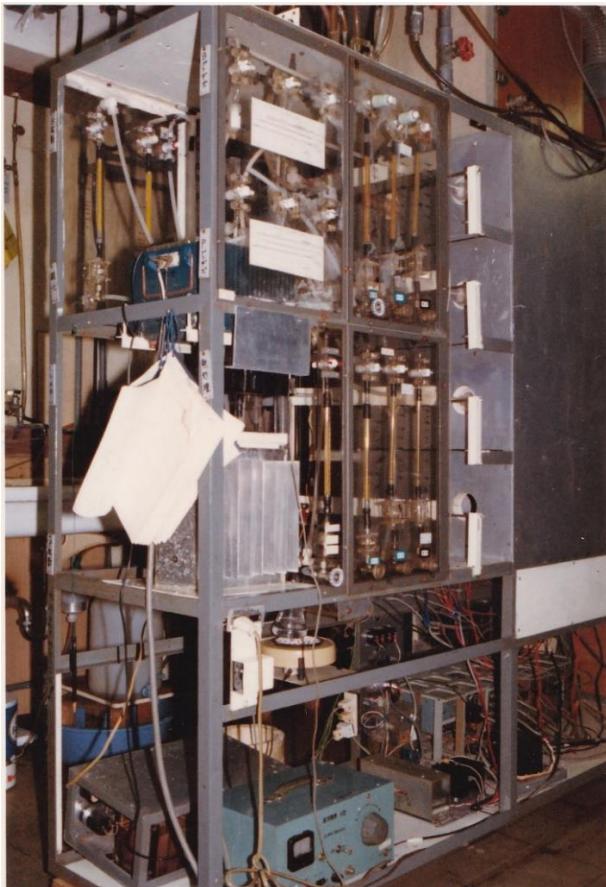
Si deep RIE (Reactive Ion Etching) system (1992)



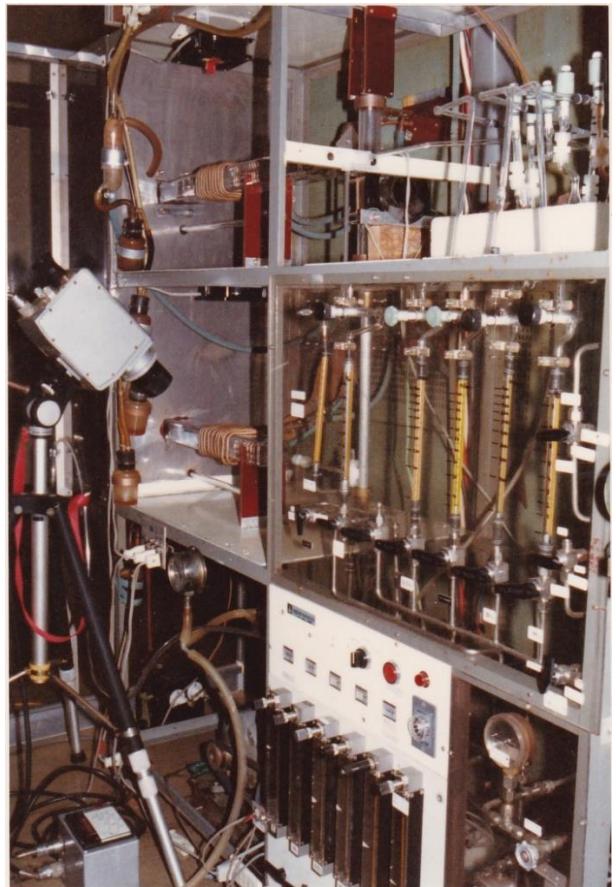
Resonating gyroscope by the deep RIE through Si wafer

(M.Takinami, K.Minami and M.Esashi : High-Speed Directional Low-Temp. Dry Etching for Bulk Silicon Micromachining, 11th Sensor Symp. (1992) 15-18)

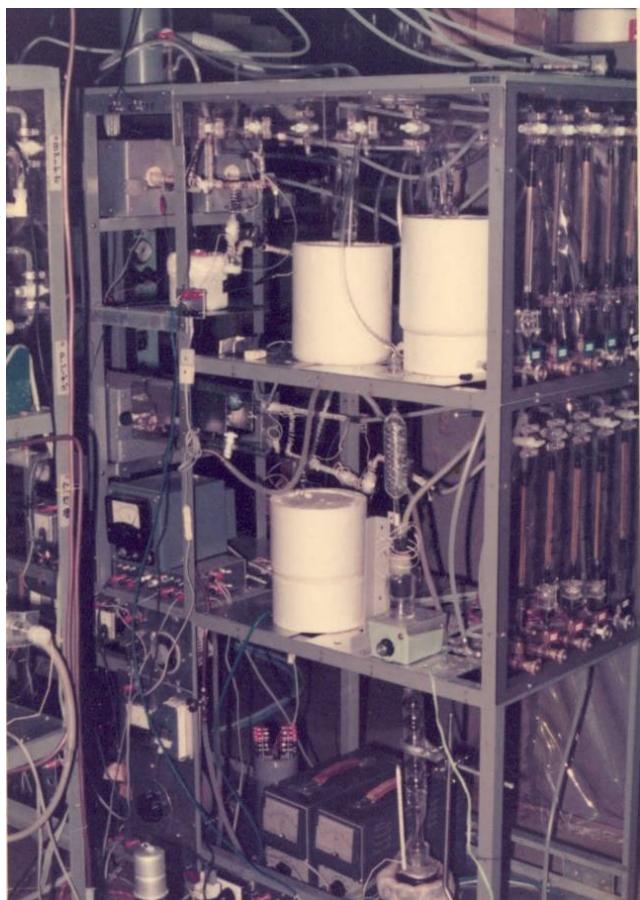
(J.Choi, K.Minami and M.Esashi : Application of Deep Reactive Ion Etching for Silicon Angular Rate Sensor, Microsystem Tech., 2, 4 (1996) 186-199)



Oxidation diffusion furnace



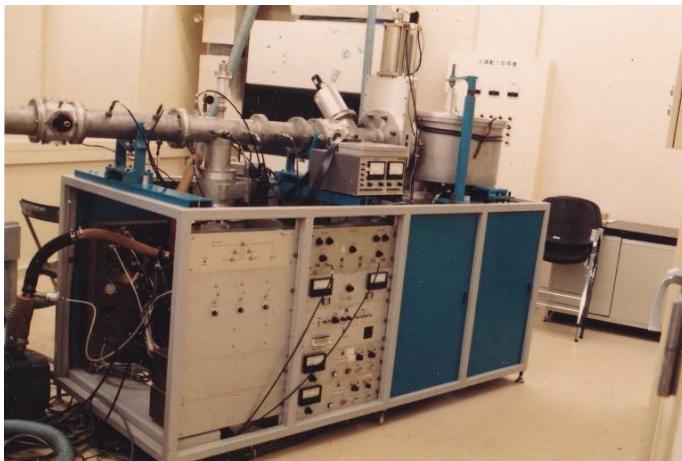
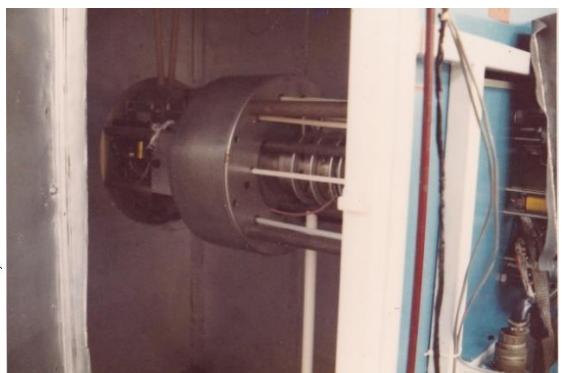
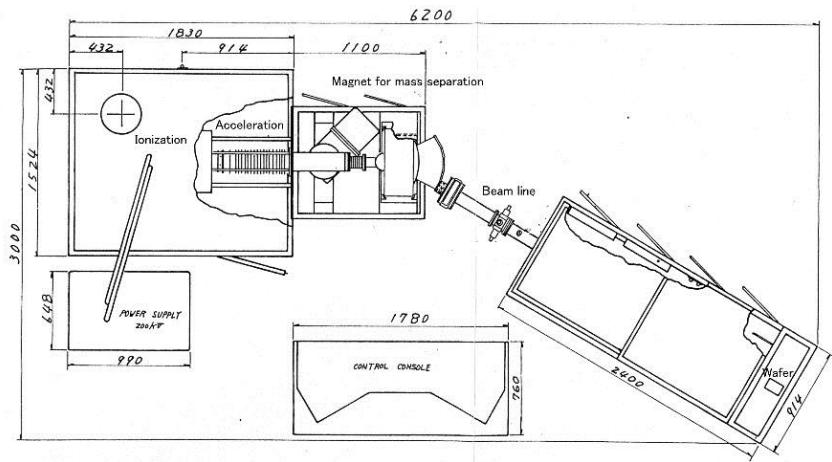
Atmospheric CVD for Si_3N_4 , SiO_2 , Poly-Si (displayed)



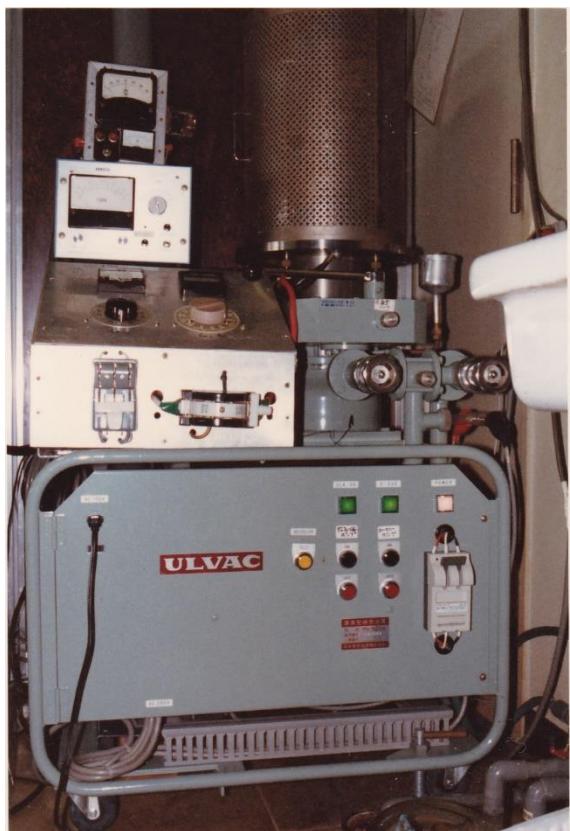
TEOS (tetraethoxysilane) source Al_2O_3 – SiO_2 CVD



Low temperature CVD for SiO_2 (displayed)



Ion implanter (Accelerator Inc, 200MP second hand)



Al, Cr-Cu-Au evaporator



Magnetron sputter deposition